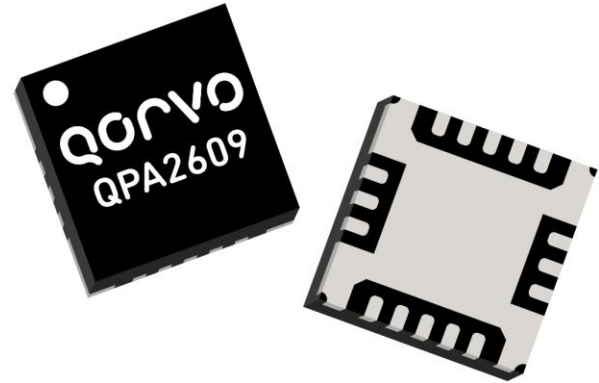


General Description

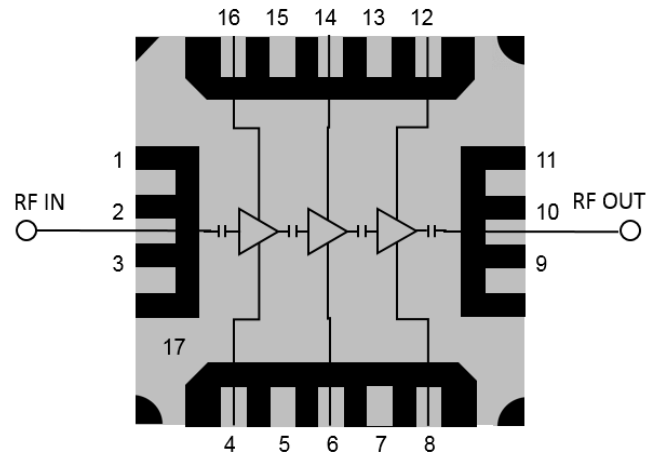
Qorvo’s QPA2609 is a packaged, high-performance, low noise amplifier fabricated on Qorvo’s production 90 nm pHEMT (QPHT09) process. Covering 7 – 14 GHz, the QPA2609 provides 26 dB small signal gain with a low noise figure of 1.1dB. The device can deliver 20dBm of power with P1dB of 18 dBm, while supporting an IM3 level of –50 dBc (at Pout=0 dBm / tone).

Packaged in a small 4 mm x 4 mm plastic overmold QFN, the QPA2609 is matched to 50 ohms with integrated DC blocking caps on both I/O ports for easy handling and simple system integration.

The QPA2609 high performance and ease of handling makes it an ideal component for satellite and point to point communication system applications.



Functional Block Diagram



Product Features

- Frequency Range: 7–14 GHz
- Noise Figure: 1.1 dB
- Small Signal Gain: 26 dB
- P1dB: 18 dBm
- IM3: –50 dBc (@ Pout=0 dBm/tone)
- Bias: $V_D = 3.5\text{ V}$, $I_{DQ} = 120\text{ mA}$, $V_G = -0.46\text{ V}$
- Plastic Overmold Package
- Package Dimensions: 4.0 x 4.0 x 0.85 mm

*Performance is typical across frequency.
Please reference electrical specification table and data plots for more details.*

Applications

- Satellite Communications
- Point to Point Communications
- Military and Commercial Radar Applications

Ordering Information

| Part No. | Description |
|-------------|--------------------------------|
| QPA2609S2 | QPA2609 Sample Bag, Qty 2 |
| QPA2609SR | QPA2609 Tape and Reel, Qty 100 |
| QPA2609TR7 | QPA2609 Tape and Reel, Qty 750 |
| QPA2609EVB1 | QPA2609 Evaluation Board |

Absolute Maximum Ratings

| Parameter | Value | Units |
|--|-------------|-------|
| Drain Voltage (V_D) | 4.5 | V |
| Drain Current ($I_{D1}/I_{D2}/I_{D3}$) | 96/115/192 | mA |
| Gate Voltage Range | -1.3 to 0 | V |
| Gate Current ($I_{G1}/I_{G2}/I_{G3}$ at 125 °C) | 5.0/5.0/6.6 | mA |
| RF Input Power (50 Ω , 85 °C) | 20 | dBm |
| Channel Temperature, T_{CH} | 175 | °C |
| Mounting Temperature (30 seconds) | 260 | °C |
| Storage Temperature | -55 to 150 | °C |

Operation of this device outside the parameter ranges given above may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied. Extended application of Absolute Maximum Rating conditions may reduce device reliability.

Recommended Operating Conditions

| Parameter | Value | Units |
|--------------------------------------|-----------|-------|
| Drain Voltage | 3.5 | V |
| Drain Current (quiescent, I_{DQ}) | 120 | mA |
| Gate Voltage (typical) | -0.46 | V |
| Operating Temperature Range | -40 to 85 | °C |

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

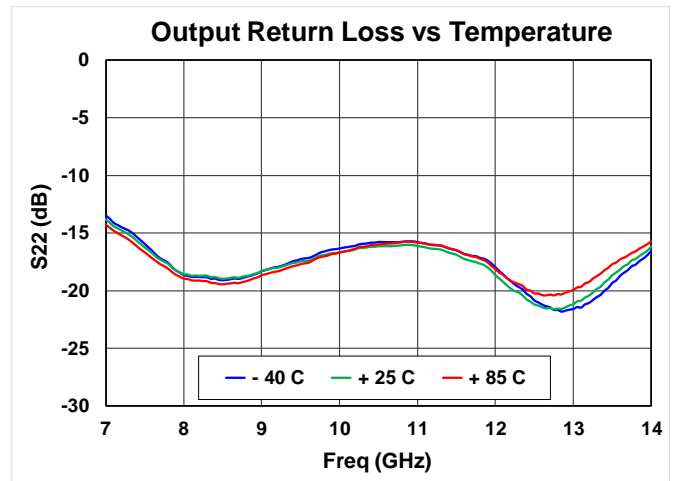
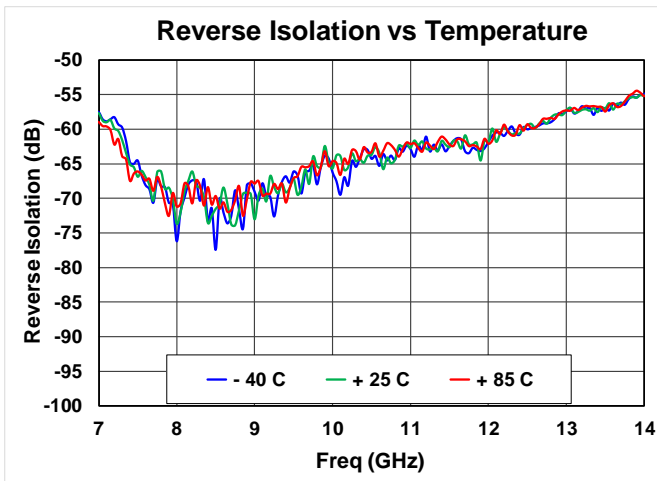
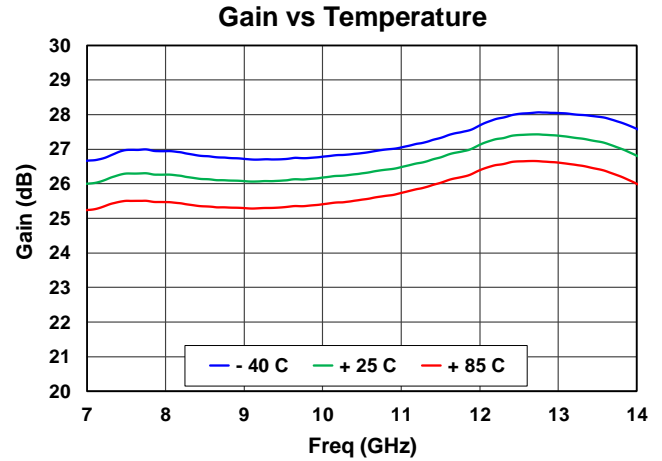
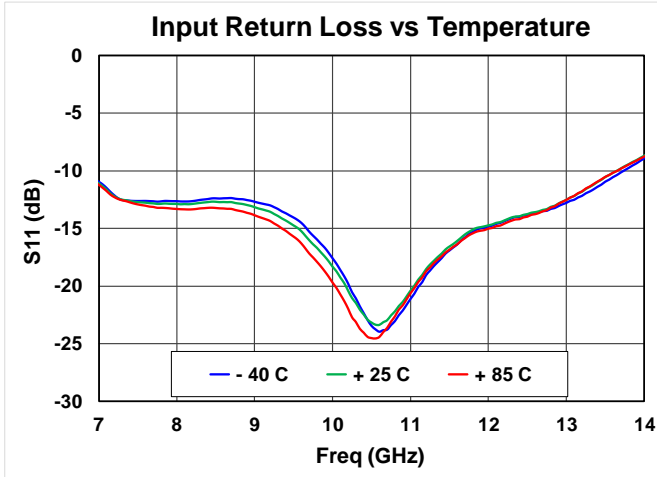
Electrical Specifications

Test Conditions unless otherwise stated: $V_D = 3.5V$, $I_{DQ} = 120mA$, 25 °C. Data de-embedded to device reference planes

| Parameter | Min | Typical | Max | Units |
|---|------|---------|-----|-------|
| Frequency | 7 | | 14 | GHz |
| Small Signal Gain (7 to 14 GHz) | | 26 | | dB |
| Small Signal Gain (8 to 12.7 GHz) | 23.5 | 26 | | dB |
| Noise Figure (7 to 14 GHz) | | 1.1 | | dB |
| Noise Figure (8 to 12.7 GHz) | | 1.1 | 1.4 | dB |
| 1-dB Compression Point | | 18 | | dBm |
| Input Return Loss | | 12 | | dB |
| Output Return Loss | | 16 | | dB |
| 3 RD Order Intermodulation level ($P_{out}=0$ dBm/tone) | | -50 | | dBc |
| Output TOI ($P_{out}=0$ dBm/tone) | | 23 | | dBm |
| Gain Temperature Coefficient | | -0.013 | | dB/°C |

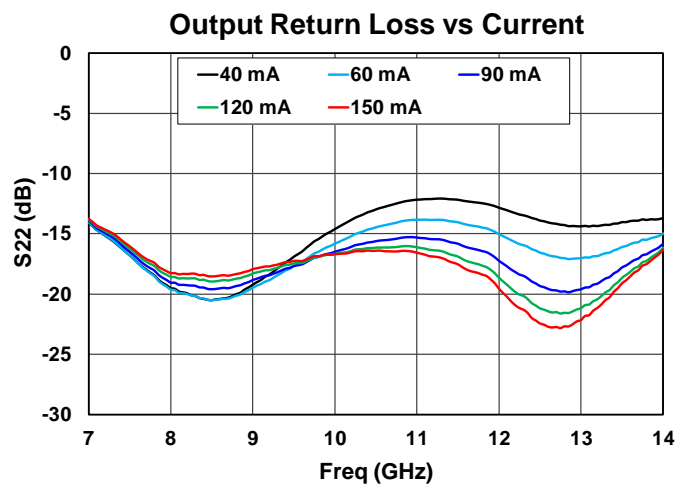
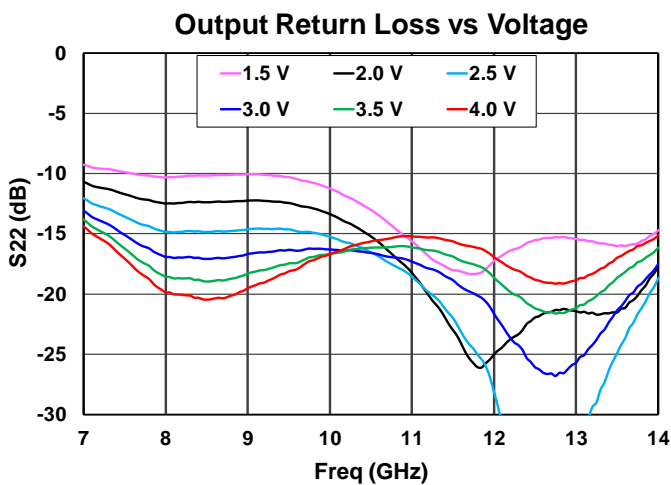
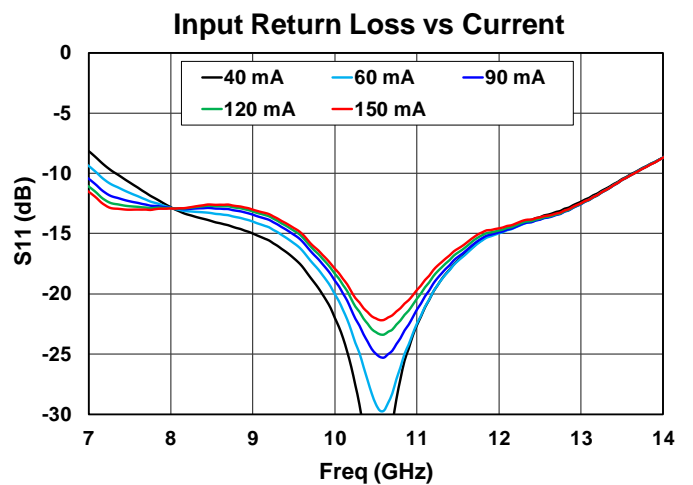
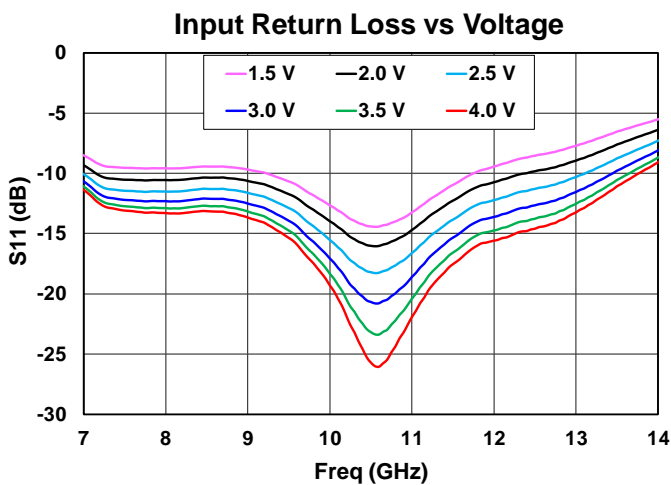
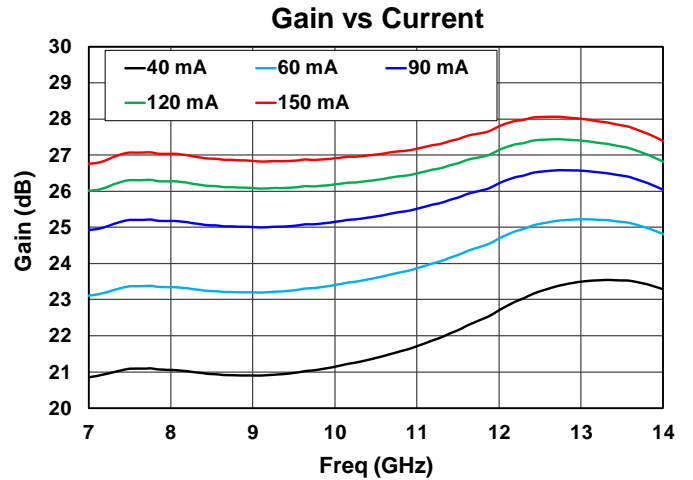
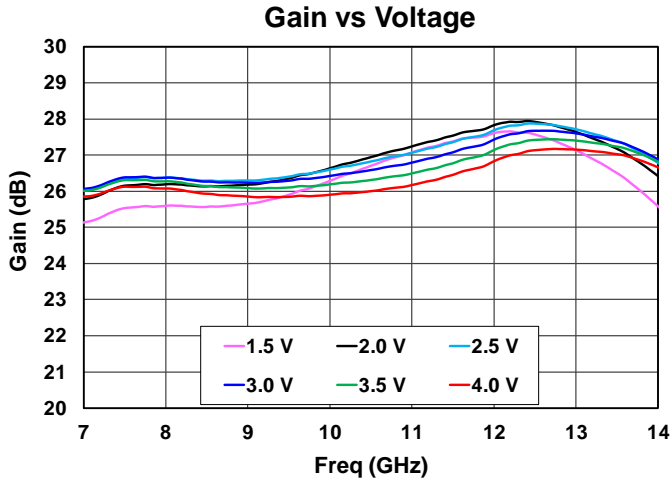
Performance Plots – Small Signal

Test Conditions unless otherwise stated: $V_D = 3.5V$, $I_{DQ} = 120mA$, $25\text{ }^\circ C$. Data de-embedded to device reference planes



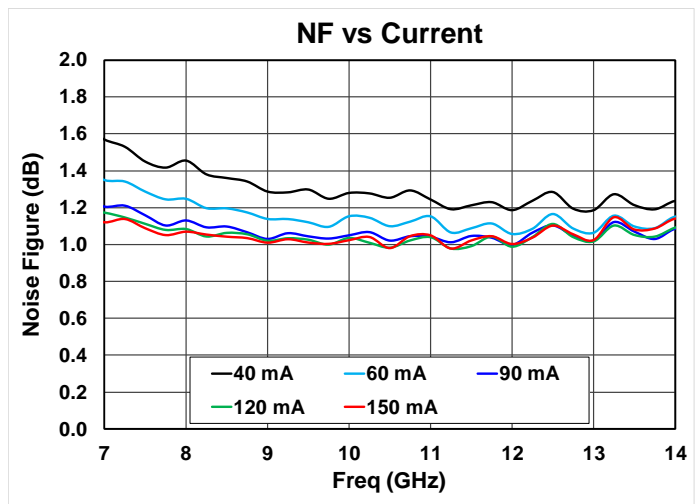
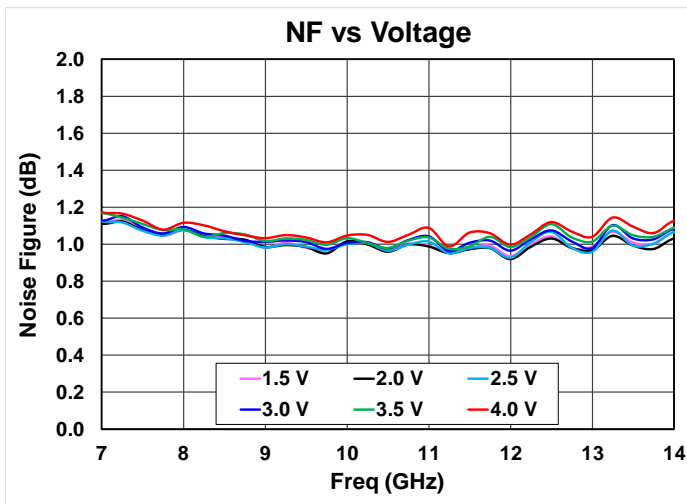
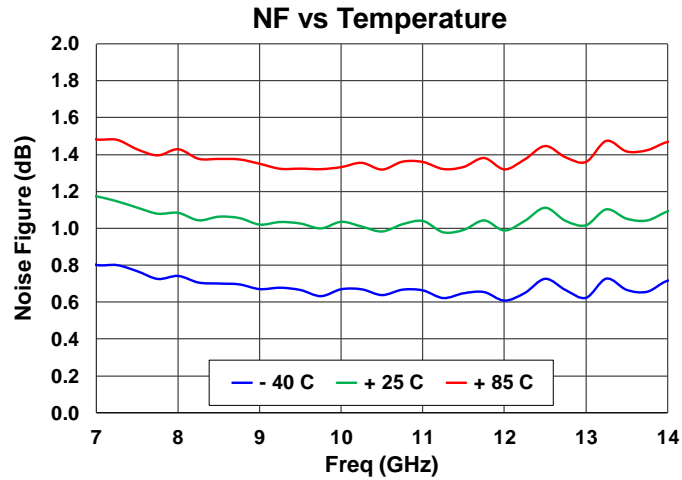
Performance Plots – Small Signal

Test Conditions unless otherwise stated: $V_D = 3.5V$, $I_{DQ} = 120mA$, $25^\circ C$. Data de-embedded to device reference planes



Performance Plots – Noise Figure

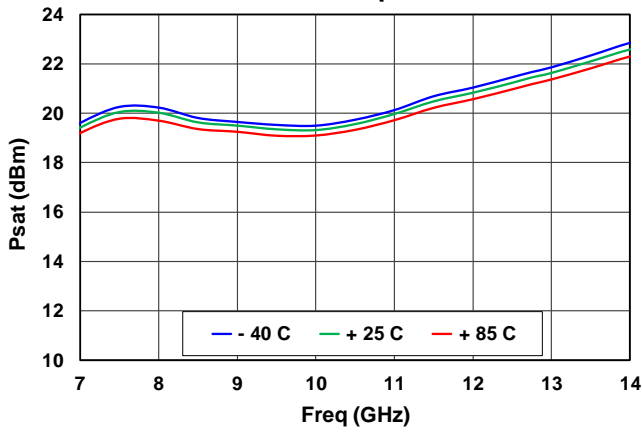
Test Conditions unless otherwise stated: $V_D = 3.5V$, $I_{DQ} = 120mA$, $25\text{ }^\circ C$. Data de-embedded to device reference planes



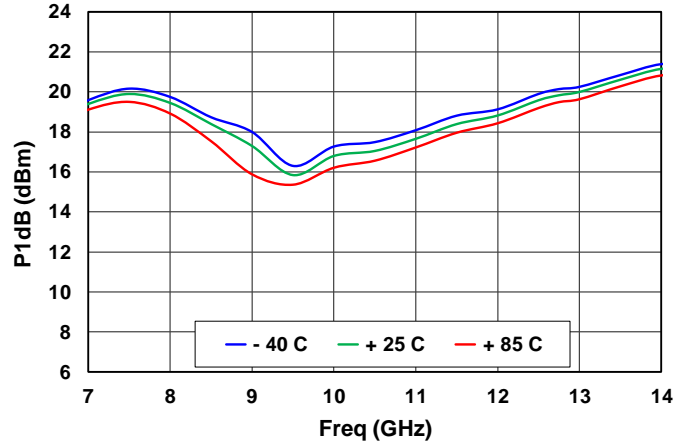
Performance Plots – Power

Test Conditions unless otherwise stated: $V_D = 3.5V$, $I_{DQ} = 120mA$, $25\text{ }^\circ C$. Data de-embedded to device reference planes

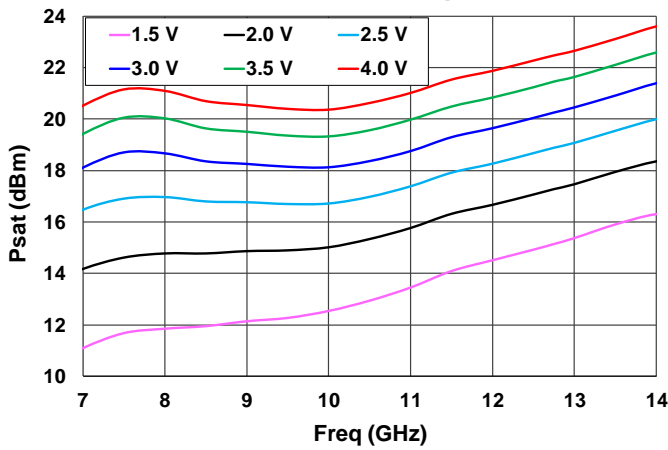
Psat vs Temperature



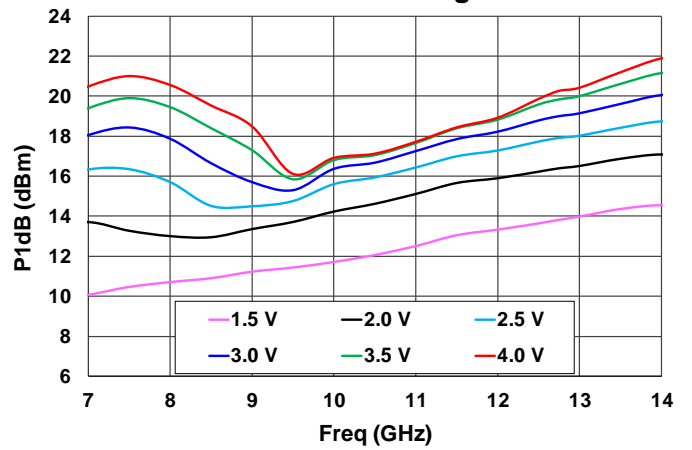
P1dB vs Temperature



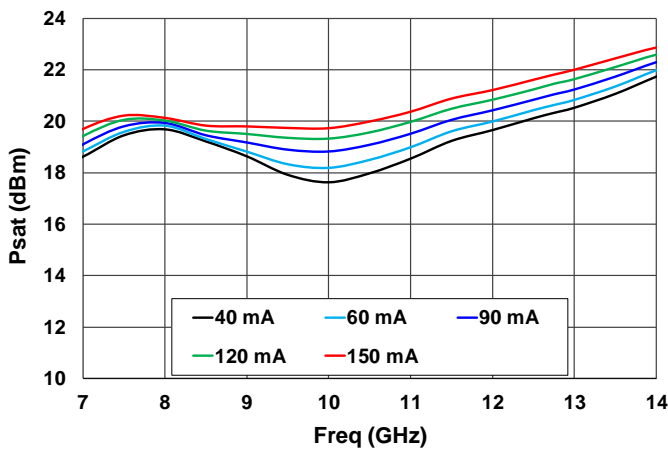
Psat vs Voltage



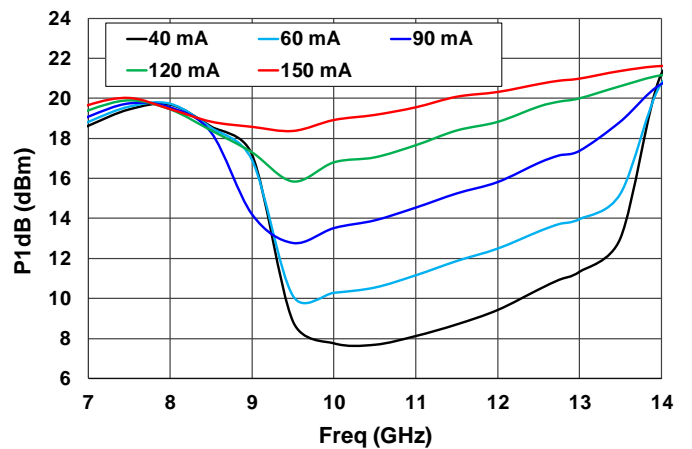
P1dB vs Voltage



Psat vs Current

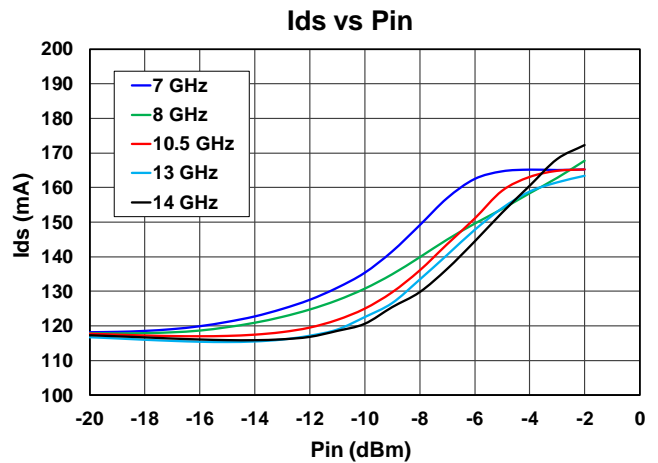
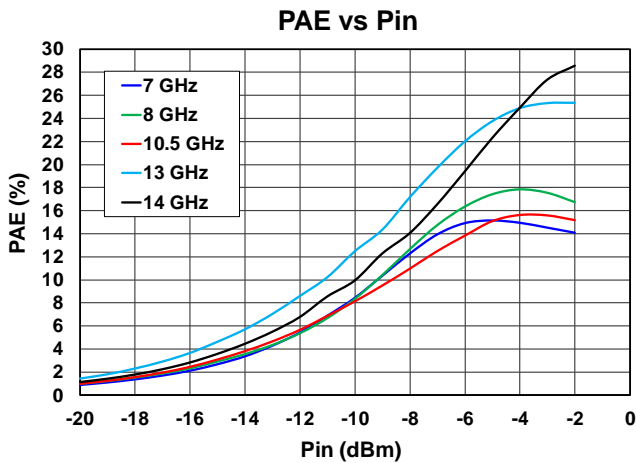
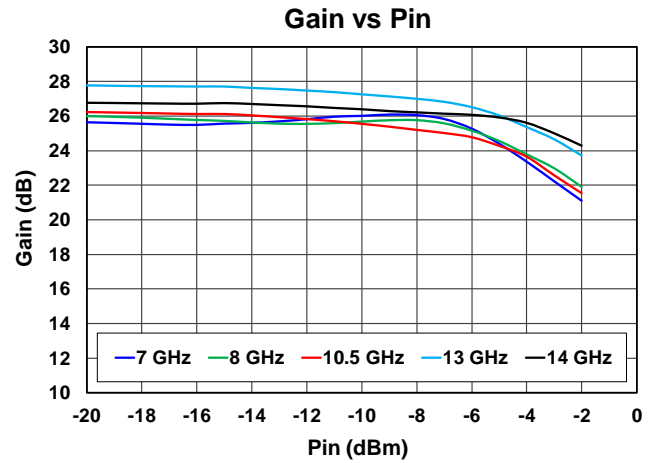
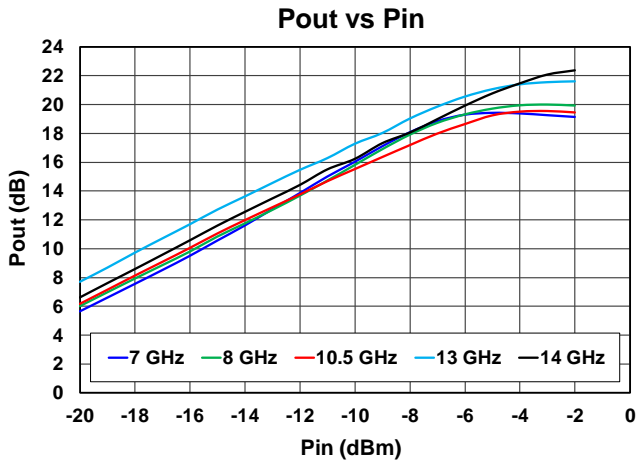


P1dB vs Current



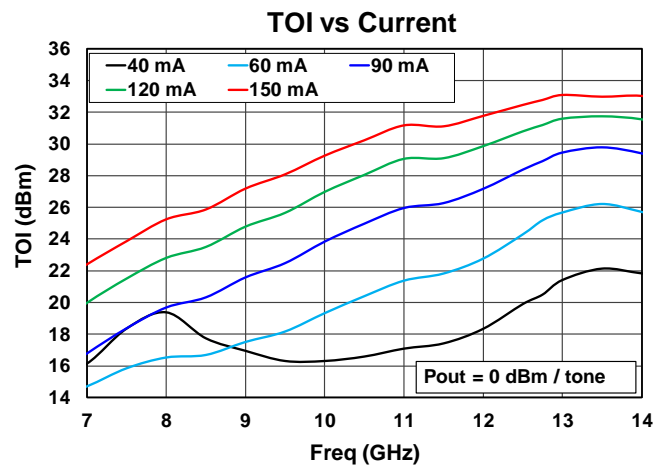
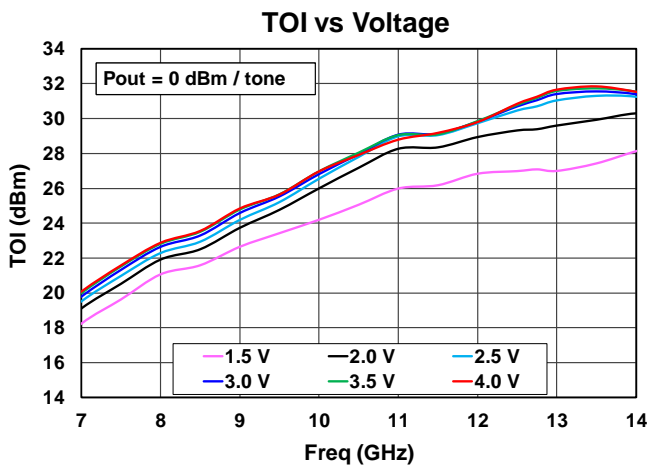
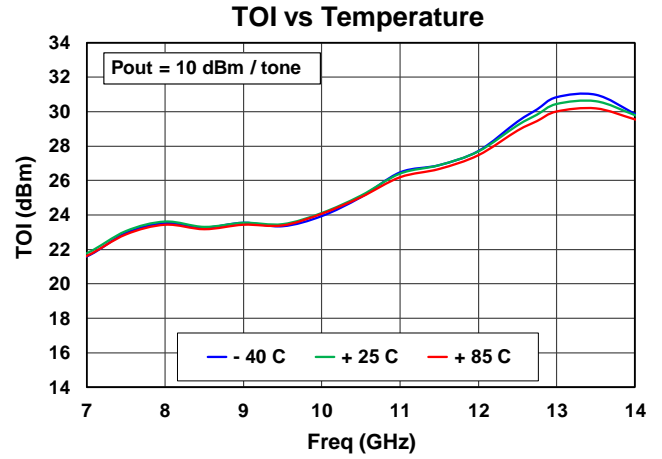
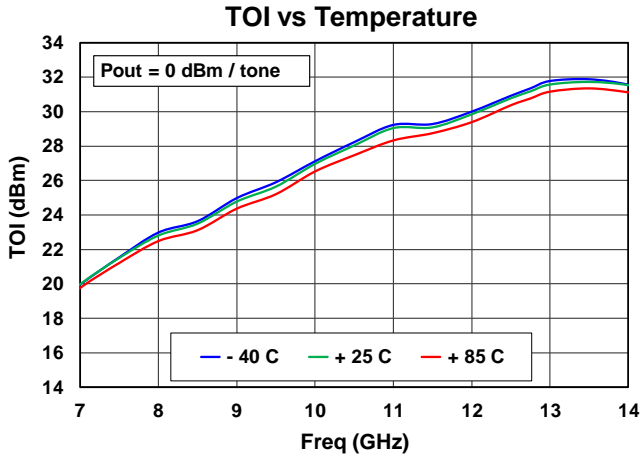
Performance Plots – Power Sweep

Test Conditions unless otherwise stated: $V_D = 3.5V$, $I_{DQ} = 120mA$, $25\text{ }^\circ C$. Data de-embedded to device reference planes



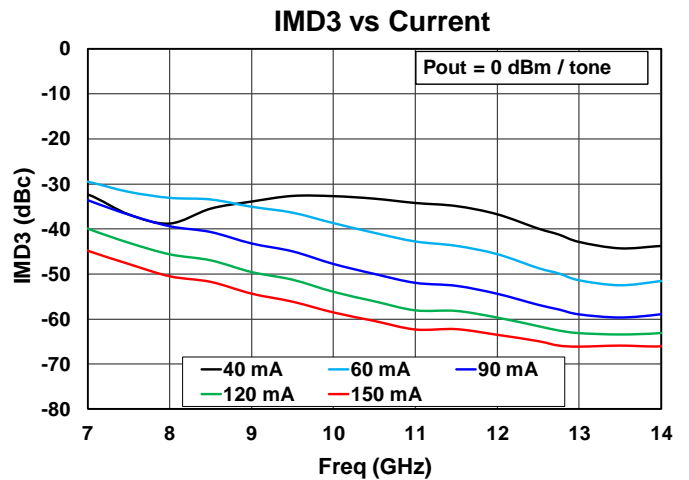
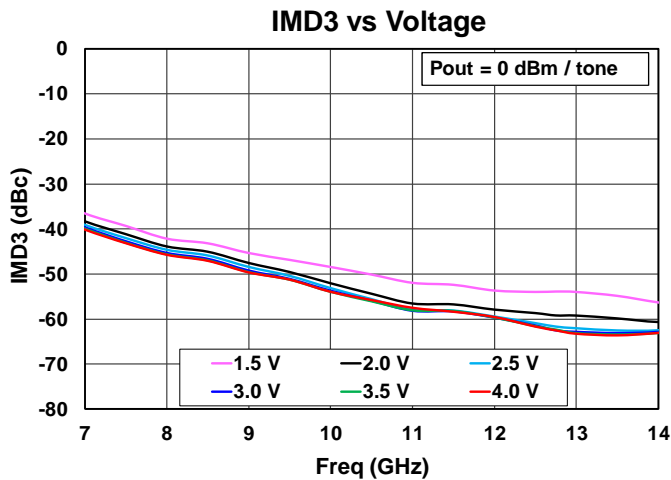
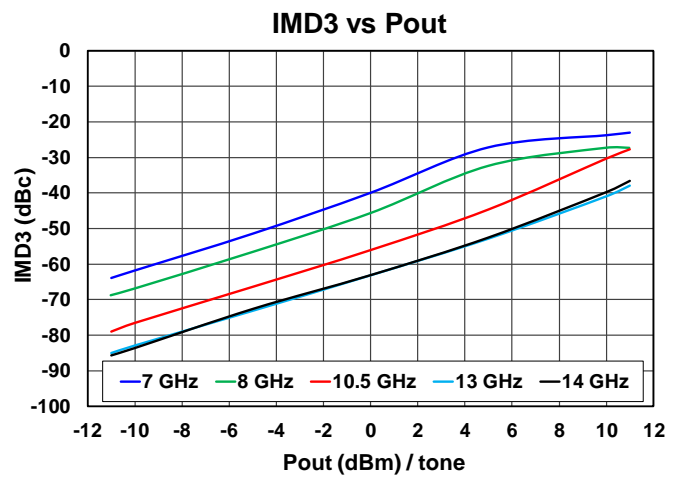
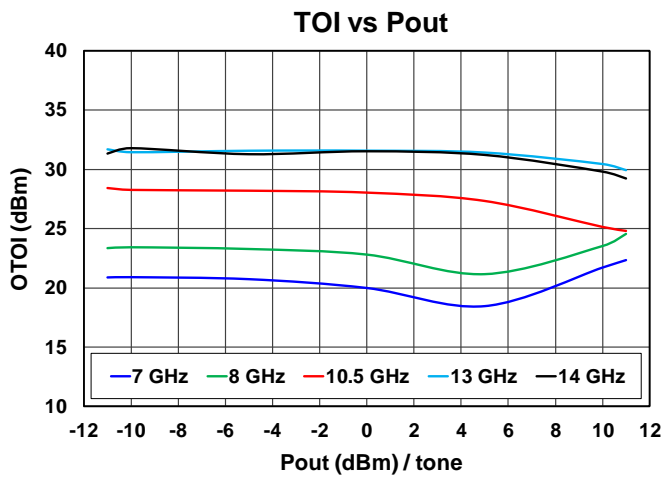
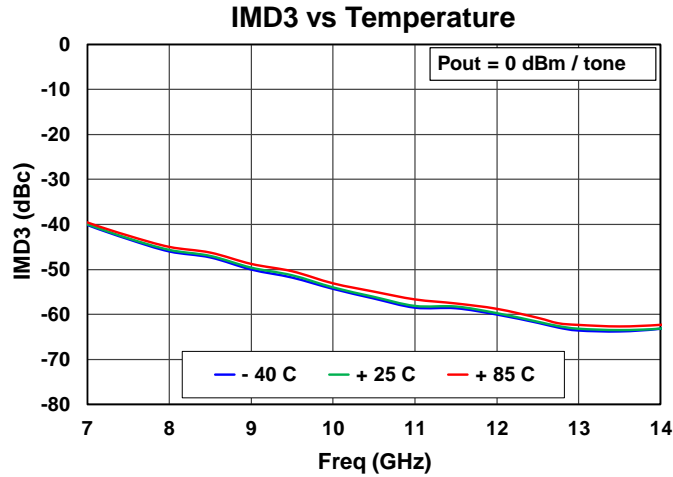
Performance Plots – Linearity

Test Conditions unless otherwise stated: $V_D = 3.5V$, $I_{DQ} = 120mA$, $\Delta f = 11\text{ MHz}$, 25°C . Data de-embedded to device reference planes



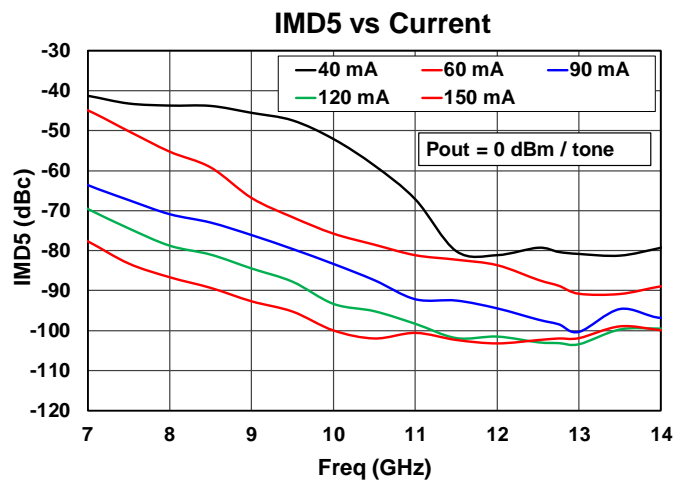
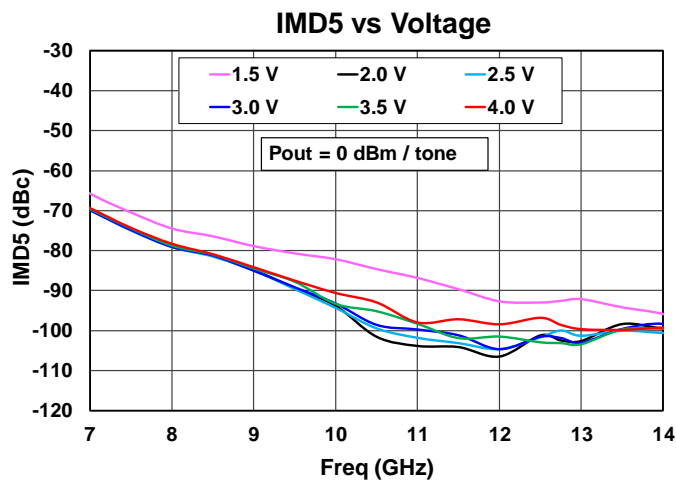
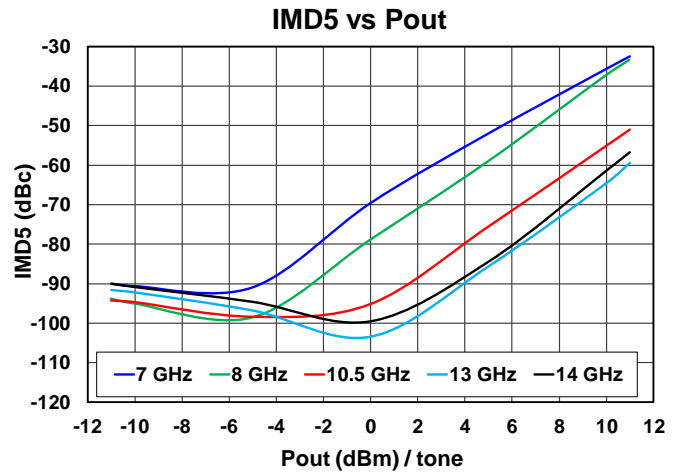
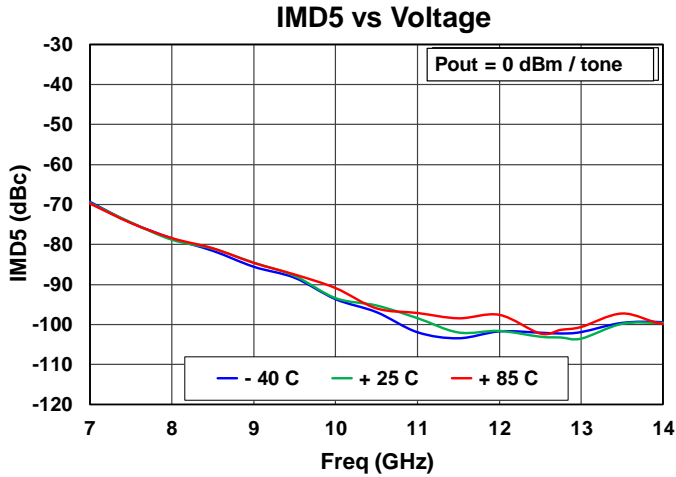
Performance Plots – Linearity

Test Conditions unless otherwise stated: $V_D = 3.5V$, $I_{DQ} = 120mA$, $\Delta f = 11\text{ MHz}$, $25\text{ }^\circ\text{C}$. Data de-embedded to device reference planes

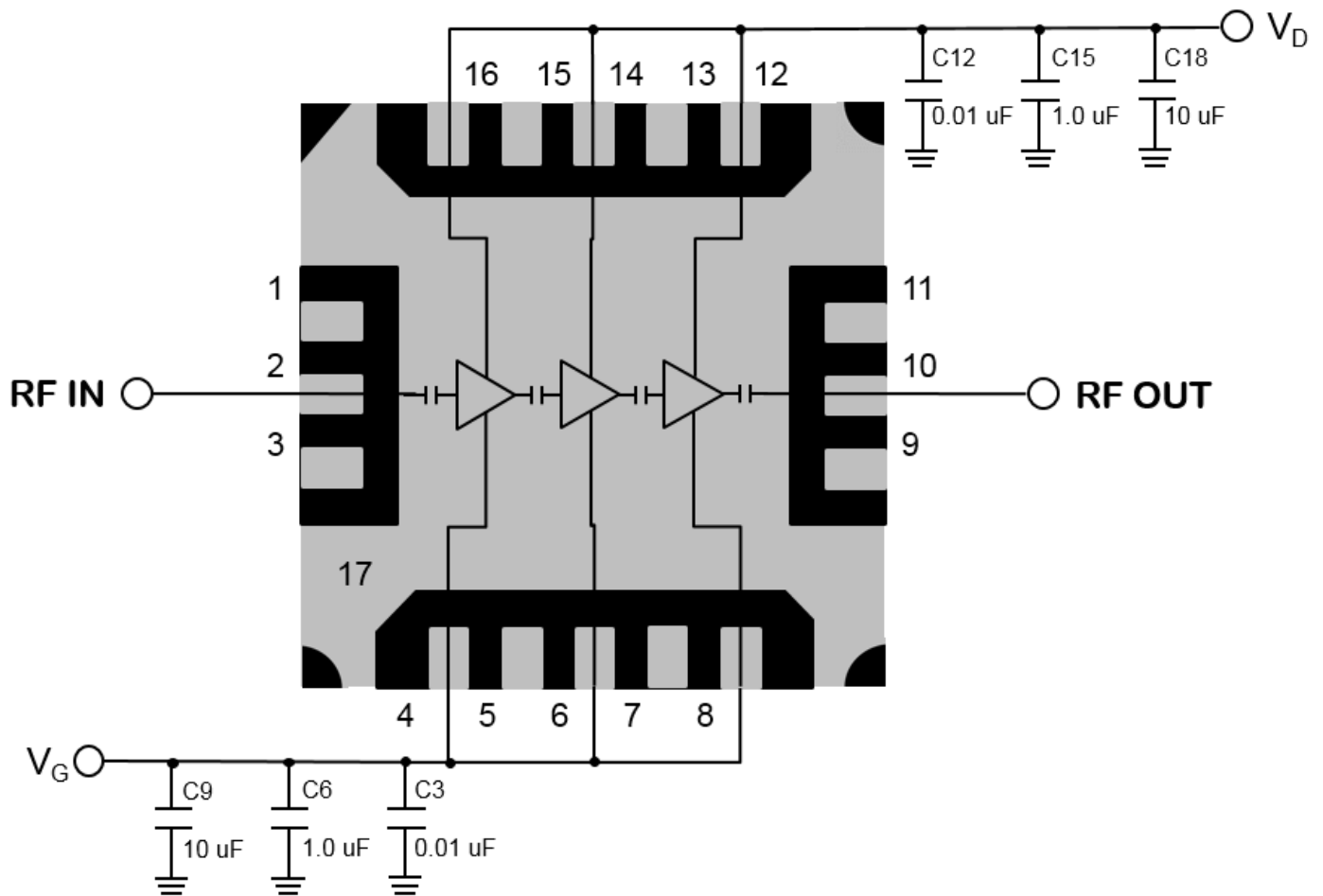


Performance Plots – Linearity

Test Conditions unless otherwise stated: $V_D = 3.5V$, $I_{DQ} = 120mA$, $\Delta f = 11\text{ MHz}$, $25\text{ }^\circ\text{C}$. Data de-embedded to device reference planes



Application Circuit



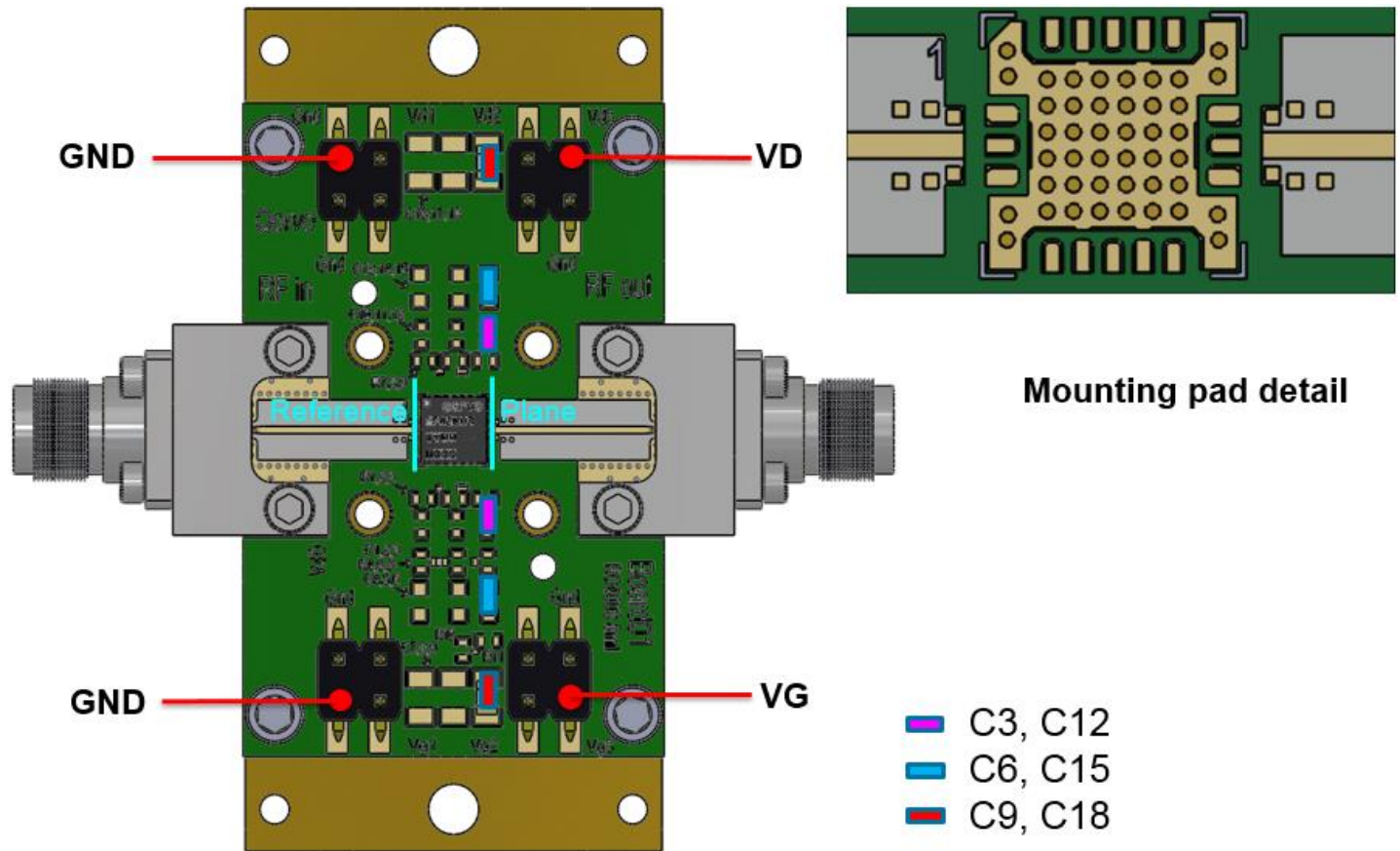
Bias-up Procedure

1. Set I_D limit to 200 mA, I_G limit to 10 mA
2. Set V_G to -1.3 V
3. Set V_D +3.5 V
4. Adjust V_G more positive until $I_{DQ} = 120$ mA ($V_G \sim -0.46$ V Typical)
5. Apply RF signal

Bias-down Procedure

1. Turn off RF signal
2. Reduce V_G to -1.3 V. Ensure $I_{DQ} \sim 0$ mA
3. Set V_D to 0 V
4. Turn off V_D supply
5. Turn off V_G supply

Evaluation Board and Assembly

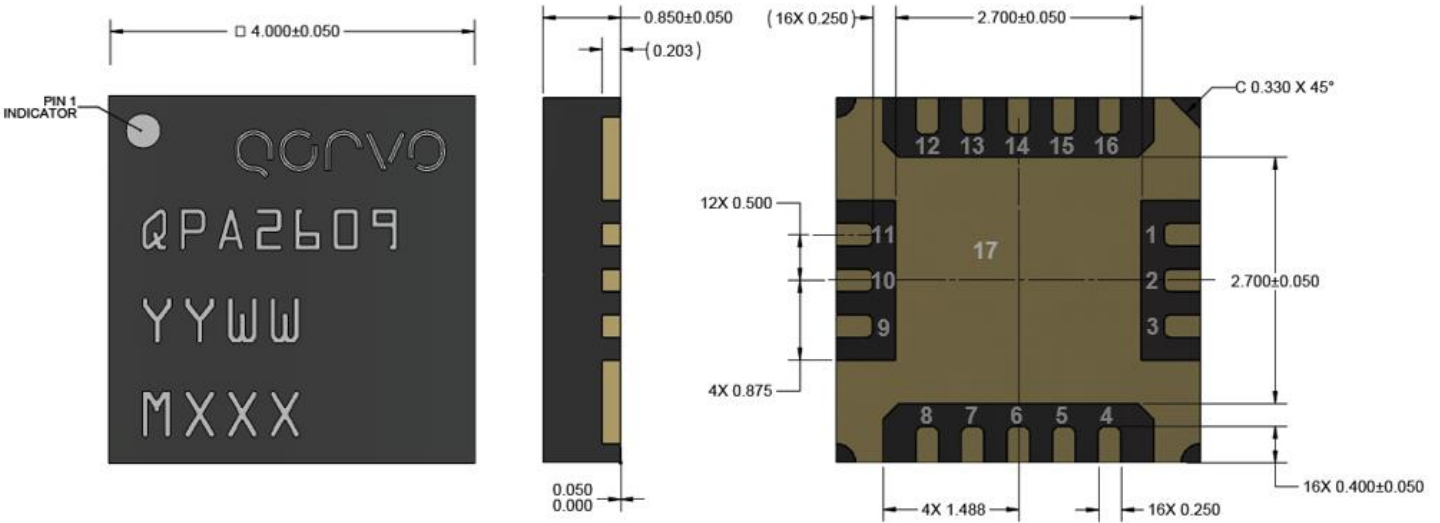


RF Layer is 0.008" thick Rogers Corp. RO4003C ($\epsilon_r = 3.35$). Metal layers are 0.5 oz. copper. The microstrip line at the connector interface is optimized for the Southwest Microwave end launch connector 1092-01A-5.

Bill of Materials

| Ref. Des. | Component | Value | Manuf. | Part Number |
|-----------|--------------------|--|---------------------|-------------|
| C3, C12 | Surface Mount Cap. | CAP 0.01UF +/-10% 50V 0402 X7R ROHS | Various | |
| C6, C15 | Surface Mount Cap. | CAP 1.0UF +/-10% 16V 0603 X7R ROHS | Various | |
| C9, C18 | Surface Mount Cap. | CAP CER 10UF 10V X7R 10% 0805 TDK ROHS | Various | |
| J1, J2 | RF Connector | 2.92 MM RF CONNECTOR | Southwest Microwave | 1092-01A-5 |

Mechanical Drawing & Pad Description



Dimensions in mm, package is mold encapsulated with NiPdAu plated leads

Part Marking: QPA2609: Part Number, YY = Part Assembly Year, WW = Part Assembly Week, MXXX = Batch ID

| Pin Number | Label | Description |
|------------------------|-----------|--|
| 1, 3, 9, 11, 17 (slug) | GND | GROUND |
| 2 | RF Input | Matched to 50 ohms, DC blocked |
| 4 | VG1 | Gate Voltage; bias network is required (V_G can be tied together at PCB) |
| 6 | VG2 | Gate Voltage; bias network is required (V_G can be tied together at PCB) |
| 8 | VG3 | Gate Voltage; bias network is required (V_G can be tied together at PCB) |
| 10 | RF Output | Matched to 50 ohms, DC blocked |
| 12 | VD3 | Drain Voltage; bias network is required (V_D can be tied together at PCB) |
| 14 | VD2 | Drain Voltage; bias network is required (V_D can be tied together at PCB) |
| 16 | VD1 | Drain Voltage; bias network is required (V_D can be tied together at PCB) |
| 5, 7, 13, 15 | N/C | No internal connection. Recommend to GND at the PCB level |

Thermal and Reliability Information

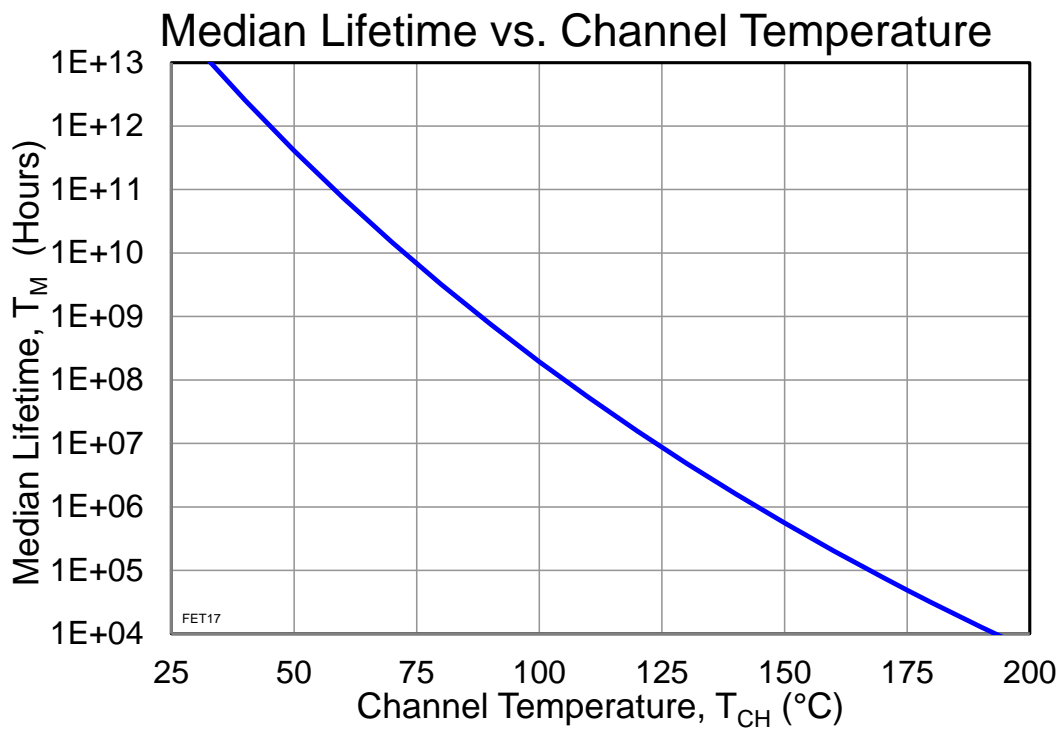
| Parameter | Test Conditions | Value | Units |
|---|--|--------|---------------|
| Thermal Resistance (θ_{JC}) ⁽¹⁾ | $T_{base} = 85^{\circ}C, V_D = 3.5 V, I_{DQ} = 120 mA$ | 47.6 | $^{\circ}C/W$ |
| Channel Temperature (T_{CH}) | Quiescent / Small Signal operation | 105 | $^{\circ}C$ |
| Median Lifetime (T_M) | $P_{DISS} = 0.42 W$ | 4.0E07 | Hrs |

Notes:

1. Thermal resistance is measured to back of the package.

Median Lifetime

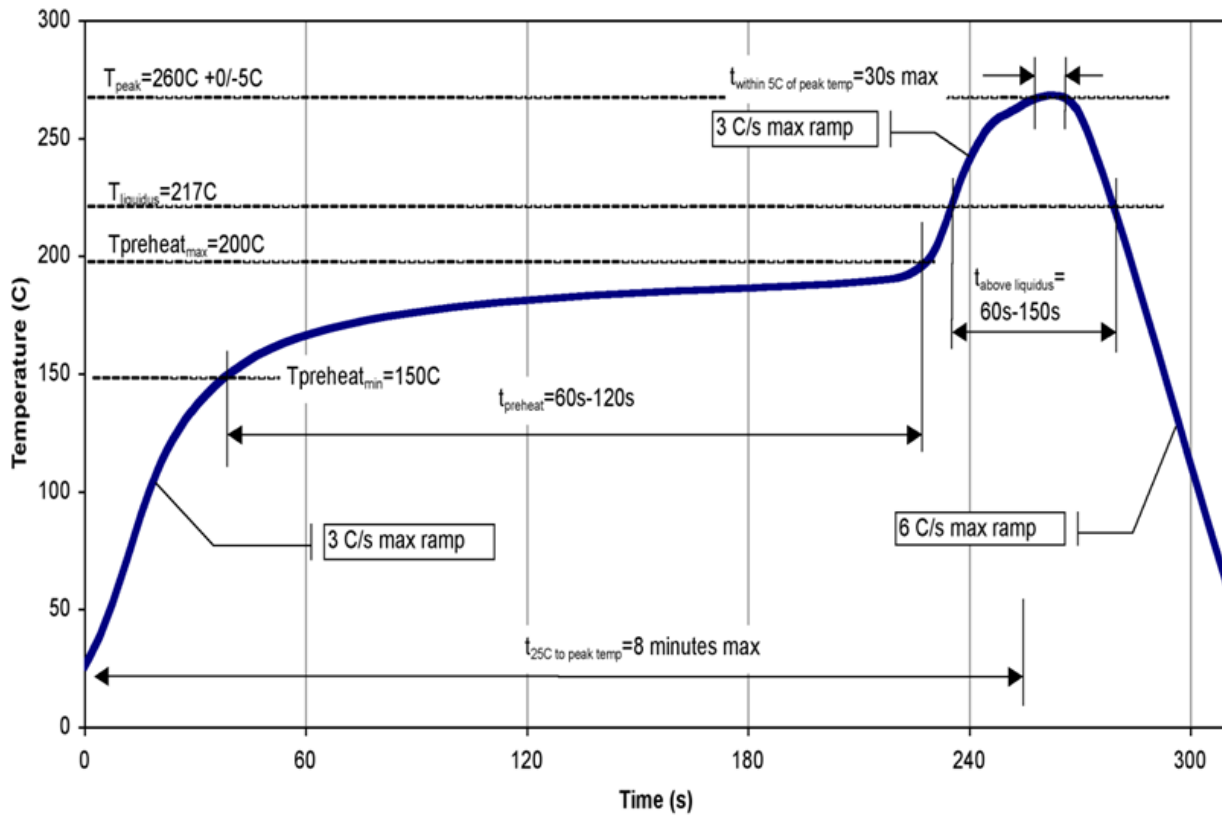
Test Conditions: $V_D = 4 V$
 Failure Criteria = 10% reduction in I_{D_MAX}



Solderability

1. Compatible with the latest version of J-STD-020, Lead-free solder, 260 °C.
2. The use of no-clean solder to avoid washing after soldering is recommended.

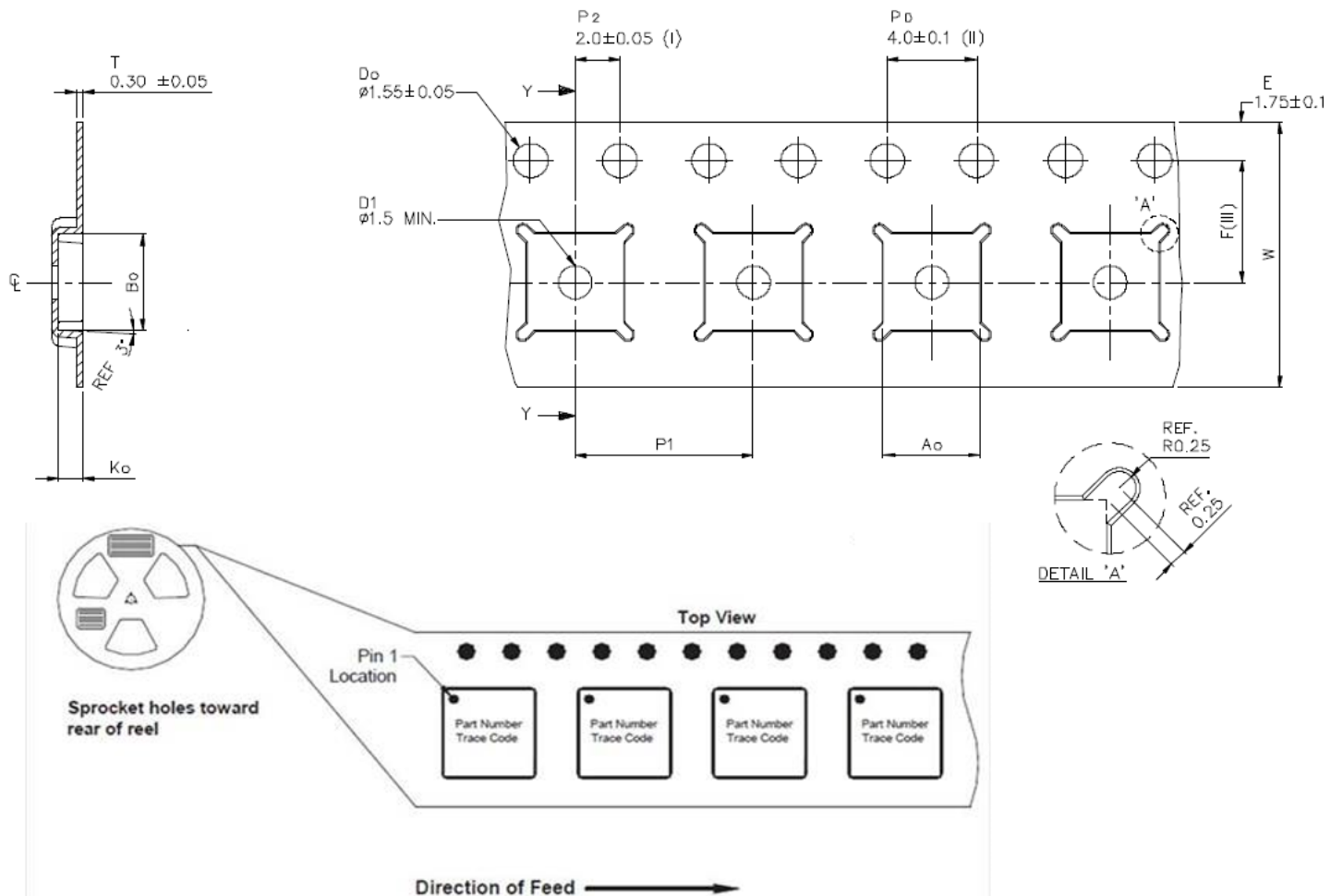
Recommended Soldering Temperature Profile



Tape and Reel Information

Standard T/R size = 750 pieces on a 7" reel.

| Material | | Cavity (mm) | | | | Distance Between Centerline (mm) | | Carrier Tape (mm) | Cover Carrier (mm) |
|----------|-----------------|-------------|------------|------------|------------|----------------------------------|---------------------|-------------------|--------------------|
| Vendor | Vendor P/N | Length (A0) | Width (B0) | Depth (K0) | Pitch (P1) | Length direction (P2) | Width Direction (F) | Width (W) | Width (W) |
| C-Pack | QFN0400 X 0400D | 4.35 | 4.35 | 1.1 | 8.0 | 2.00 | 5.50 | 12.0 | 9.20 |



Handling Precautions

| Parameter | Rating | Standard |
|----------------------------------|--------|------------------------------------|
| ESD – Human Body Model (HBM) | 1A | ESDA / JEDEC JS-001-2012 |
| ESD – Charged Device Model (CDM) | C3 | ESDA / JEDEC JS-002-2014 |
| MSL – Convection Reflow 260 °C | 3 | JEDEC standard IPC/JEDEC J-STD-020 |



Caution!
ESD-Sensitive Device

RoHS Compliance

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU.

This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C₁₅H₁₂Br₄O₂) Free
- SVHC Free

Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

Tel: 1-844-890-8163

Web: www.qorvo.com

Email: customer.support@qorvo.com

For technical questions and application information: **Email:** appsupport@qorvo.com

Important Notice

The information contained herein is believed to be reliable; however, Qorvo makes no warranties regarding the information contained herein and assumes no responsibility or liability whatsoever for the use of the information contained herein. All information contained herein is subject to change without notice. Customers should obtain and verify the latest relevant information before placing orders for Qorvo products. The information contained herein or any use of such information does not grant, explicitly or implicitly, to any party any patent rights, licenses, or any other intellectual property rights, whether with regard to such information itself or anything described by such information. **THIS INFORMATION DOES NOT CONSTITUTE A WARRANTY WITH RESPECT TO THE PRODUCTS DESCRIBED HEREIN, AND QORVO HEREBY DISCLAIMS ANY AND ALL WARRANTIES WITH RESPECT TO SUCH PRODUCTS WHETHER EXPRESS OR IMPLIED BY LAW, COURSE OF DEALING, COURSE OF PERFORMANCE, USAGE OF TRADE OR OTHERWISE, INCLUDING THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE.**

Without limiting the generality of the foregoing, Qorvo products are not warranted or authorized for use as critical components in medical, life-saving, or life-sustaining applications, or other applications where a failure would reasonably be expected to cause severe personal injury or death.

Copyright 2020 © Qorvo, Inc. | Qorvo is a registered trademark of Qorvo, Inc.